

DB Plastic-Encapsulate Bridge Rectifier

General Purpose Bridge Rectifier

Features:

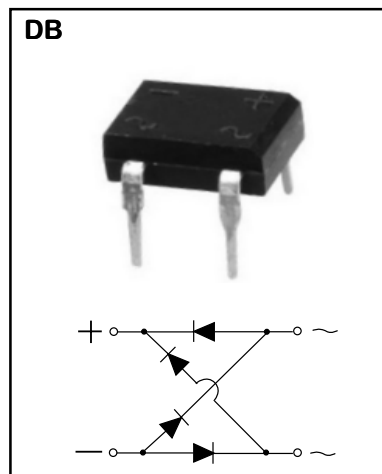
- $I_{F(AV)}$ 2A
- V_{RRM} 50V-1000V
- High surge current capability
- Glass passivated chip

Applications:

- General purpose 1 phase Bridge rectifier applications

Marking

- DB20XG
X : From 01 To 7



Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	DB2						
				01G	02G	03G	04G	05G	06G	07G
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	V_{RMS}	V		35	70	140	280	420	560	700
Average Rectified Output Current	I_o	A	60Hz sine wave, R-load, $T_a=25^\circ\text{C}$	On glass-epoxi substrate		2.0				
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz halfsine wave, 1 cycle, $T_j=25^\circ\text{C}$		75					
Current Squared Time	I^2t	A^2S	$1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$, Rating of per diode		23.7					
Operation Junction and Storage Temperature Range	T_j, T_{stg}	$^\circ\text{C}$	-55 ~ +150							

Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	$I_{FM}=2.0\text{A}$, Pulse measurement, Rating of per diode	1.0
Peak Reverse Current	I_{RRM}	μA	$V_{RM}=V_{RRM}$, Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{\theta J-A}$	$^\circ\text{C}/\text{W}$	Between junction and ambient, On glass-epoxi substrate	25
	$R_{\theta J-L}$		Between junction and lead	15

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

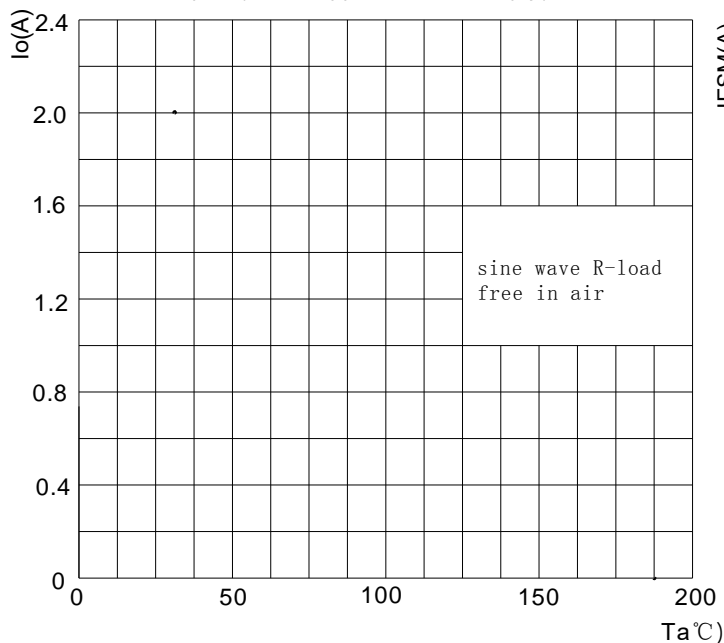


FIG.2: MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

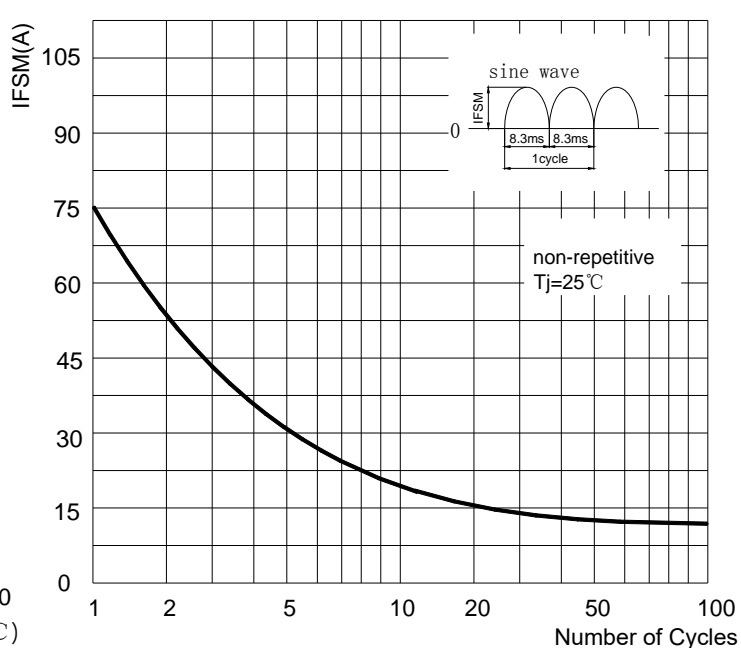


FIG.3: TYPICAL FORWARD CHARACTERISTICS

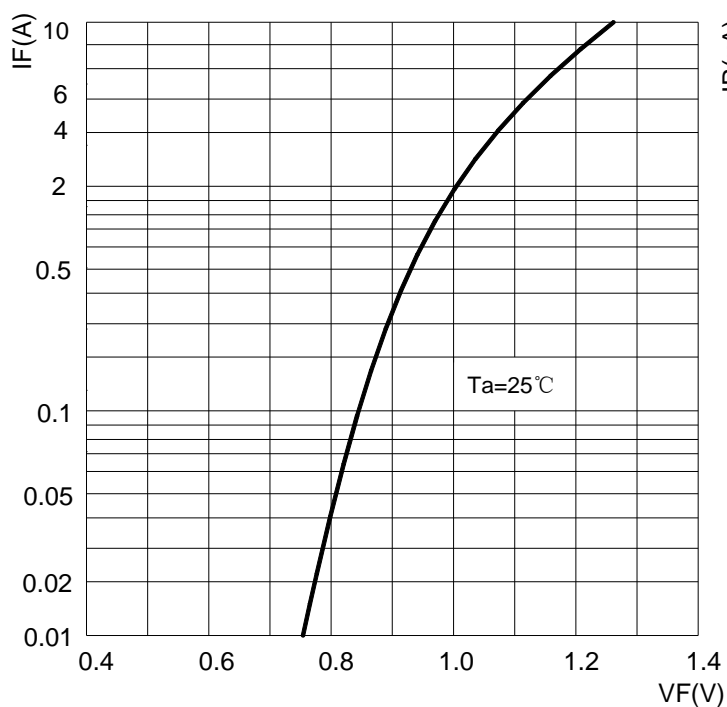
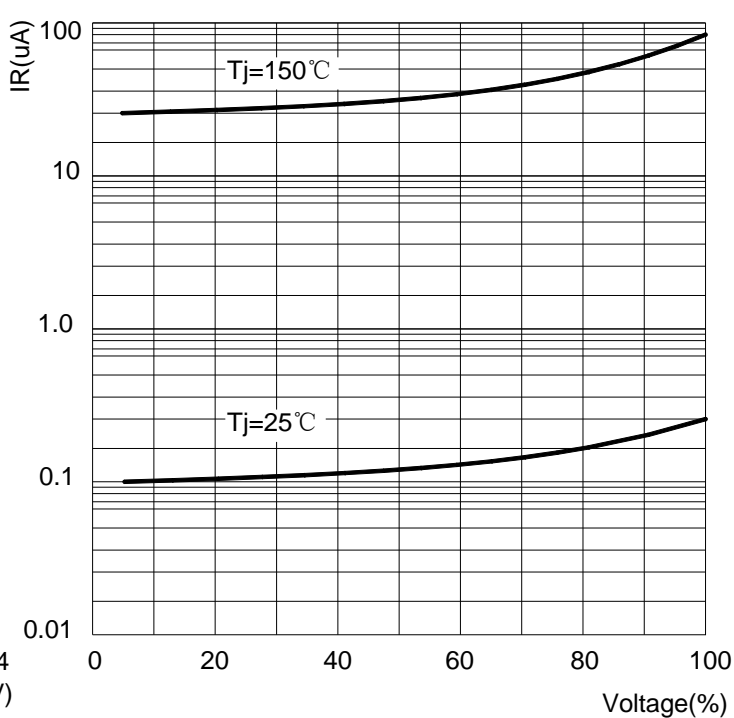
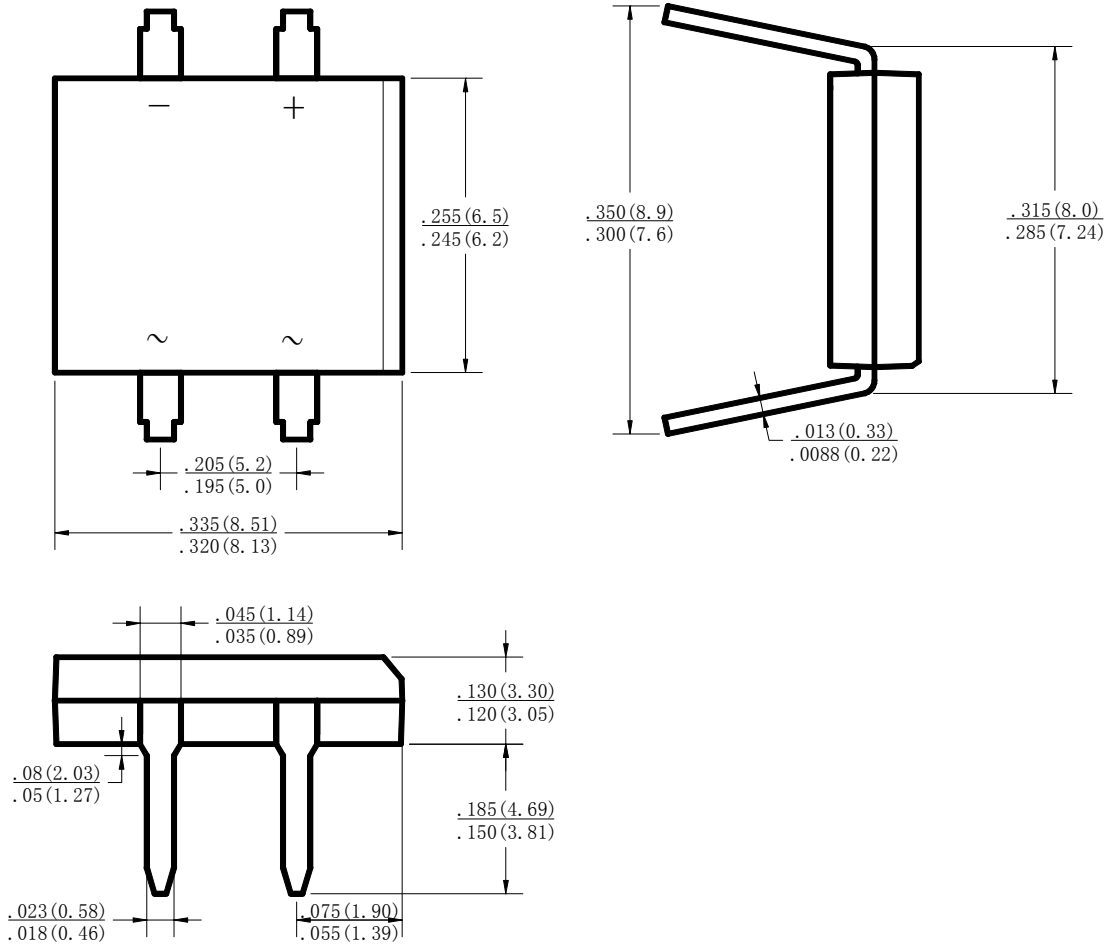


FIG.4: TYPICAL REVERSE CHARACTERISTICS



DB-1 Package Outline Dimensions



Dimensions in inches and (millimeters)